

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims

1. (Currently Amended) An organic electroluminescent device, comprising:
a first electrode;
a second electrode; and
one or more organic luminescent media, including an emission layer, wherein the emission layer comprises:
a doping layer having both host material and doping material; and
a non-doping layer having only said host material, wherein at least a portion of the non-doping layer is in contact with at least a portion of the doping layer, and wherein a thickness of said doping layer of the emission layer is greater than ~~or equal to~~ a thickness of said non-doping layer of the emission layer, and wherein said non-doping layer has a thickness of approximately 1~15 nm.
2. (Canceled)
3. (Canceled)
4. (Previously Presented) The device of claim 1, wherein said doping layer of the emission layer has a thickness of 1~60nm.

5. (Previously Presented) The device of claim 1, wherein said one or more organic luminescent media includes a hole injection layer, a hole transport layer, an electron injection layer, and an electron transport layer, and wherein said doping layer of the emission layer is in contact with any one of said first electrode, said hole injection layer, and said hole transport layer, and said non-doping layer of the emission layer is in contact with any one of said second electrode, said electron injection layer, and said electron transport layer.

6. (Currently Amended) A method for making an organic electroluminescent device, comprising:

forming an anode, a hole injection layer, and a hole transport layer sequentially on a substrate;

forming an emission layer that includes a doping layer and a non-doping layer, wherein a thickness of said doping layer of the emission layer is greater than ~~or equal to~~ a thickness of said non-doping layer of the emission layer, and wherein said non-doping layer has a thickness of approximately 1~15 nm; and

forming an electron injection layer, an electron transport layer, and a cathode sequentially on the emission layer.

7. (Currently Amended) A method for making an organic electroluminescent device, comprising:

forming an anode on a substrate;

forming one or more hole-related layers on the anode;

forming an emission layer that includes a doping layer and a separate non-doping layer, wherein a thickness of said doping layer of the emission layer is greater than ~~or equal to~~ a thickness of said non-doping layer of the emission layer, and wherein said non-doping layer has a thickness of approximately 1~15 nm;

forming one or more electron-related layers on the emission layer; and

forming a cathode on the one or more electron related layers.

8. (New) The device of claim 1, wherein the thickness of the doping layer is more than 20 times greater than the thickness of the non-doping layer.

9. (New) The device of claim 1, wherein the thickness of the doping layer is more than 10 times greater than a thickness of the non-doping layer.

10. (New) The device of claim 1, wherein the thickness of the non-doping layer is equal to or less than half the thickness of the doping layer.

11. (New) The device of claim 1, wherein the thickness of the non-doping layer is equal to or less than 75% the thickness of the doping layer.

12. (New) The device of claim 1, wherein the thickness of the non-doping layer is approximately 1 – 4.5nm.

13. (New) The device of claim 6, wherein the thickness of the doping layer is more than 20 times greater than the thickness of the non-doping layer.

14. (New) The device of claim 6, wherein the thickness of the doping layer is more than 10 times greater than a thickness of the non-doping layer.

15. (New) The device of claim 6, wherein the thickness of the non-doping layer is equal to or less than half the thickness of the doping layer.

16. (New) The device of claim 6, wherein the thickness of the non-doping layer is equal to or less than 75% the thickness of the doping layer.

17. (New) The device of claim 6, wherein a thickness of the non-doping layer is approximately 1 - 4.5nm.

18. (New) The device of claim 7, wherein the thickness of the doping layer is more than 20 times greater than the thickness of the non-doping layer.

19. (New) The device of claim 7, wherein the thickness of the doping layer is more than 10 times greater than a thickness of the non-doping layer.

20. (New) The device of claim 7, wherein the thickness of the non-doping layer is equal to or less than half the thickness of the doping layer.

21. (New) The device of claim 7, wherein the thickness of the non-doping layer is equal to or less than 75% the thickness of the doping layer.

22. (New) The device of claim 7, wherein a thickness of the non-doping layer is approximately 1 - 4.5nm.